



YOUSHANG SEMICONDUCTOR

**设计研发新型功率器件**

**各类小信号开关**

**中低压及高压大电流等场效应管**

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企业微信二维码



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## Product Summary

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>A</sub> = +25°C
30V	60mΩ @ V <sub>GS</sub> = 10V	2.7A
	100mΩ @ V <sub>GS</sub> = 4.5V	2.1A

## Features and Benefits


- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed

## Description and Applications

This MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

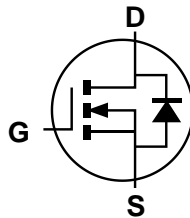
- General Purpose Interfacing Switch
- Power Management Functions
- DC-DC Converters
- Analog Switch

## Mechanical Data

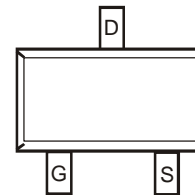
- Case: SOT323
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish—Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 
- Weight: 0.027 grams (Approximate)



Top View



Equivalent Circuit



Top View

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V <sub>DSS</sub>	30	V
Gate-Source Voltage			V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V	Steady State	T <sub>A</sub> = +25°C	I <sub>D</sub>	2.7	A
		T <sub>A</sub> = +70°C		2.2	
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)			I <sub>DM</sub>	22	A
Maximum Body Diode Forward Current (Note 5)			I <sub>S</sub>	0.67	A

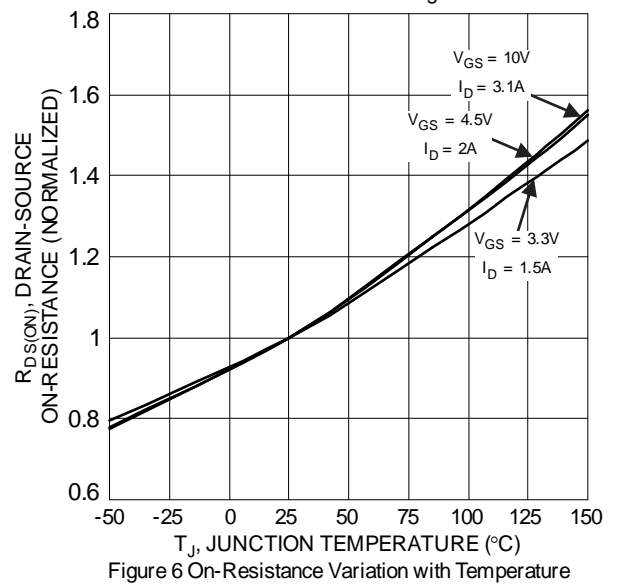
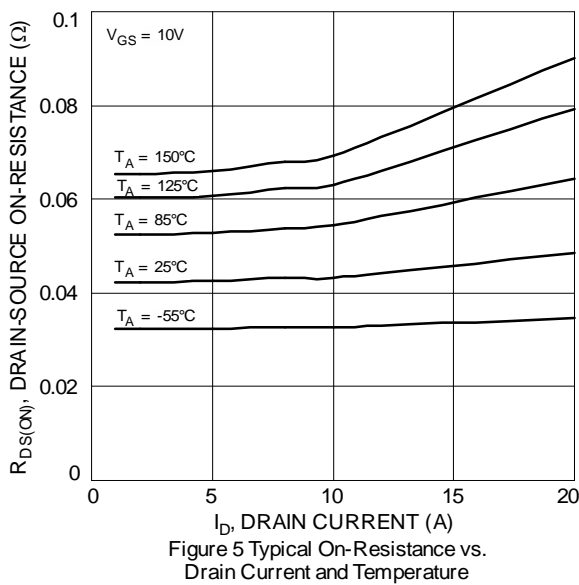
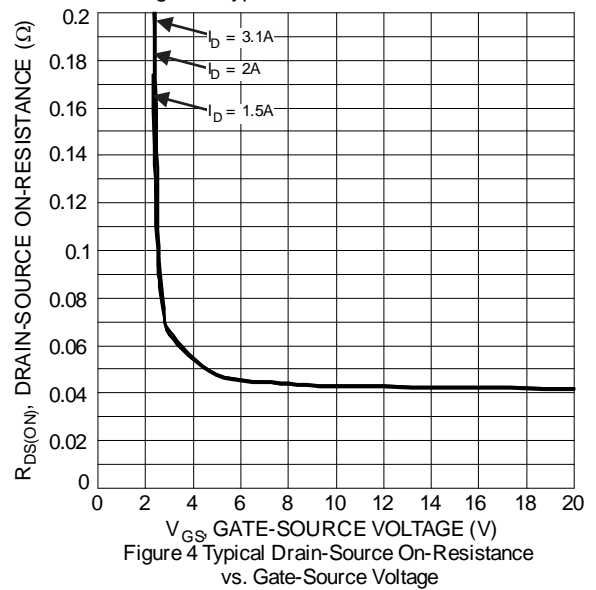
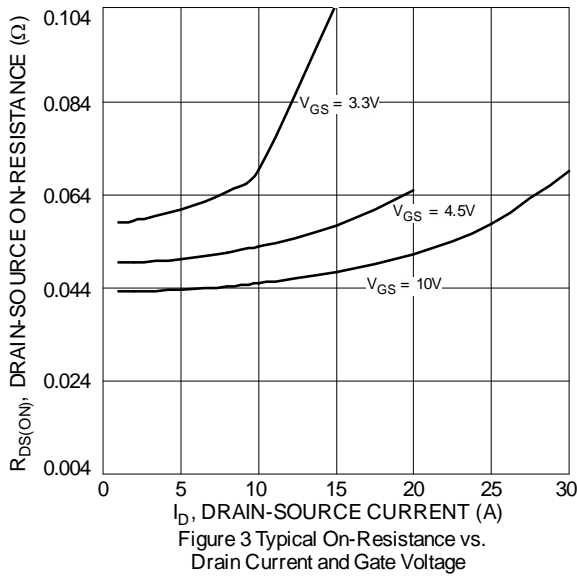
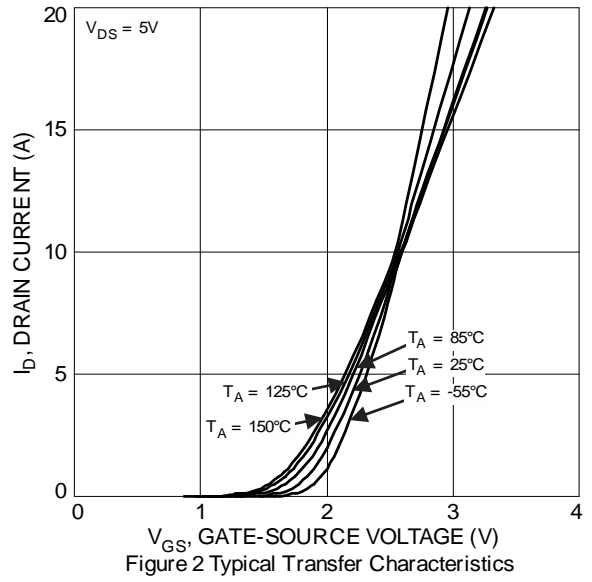
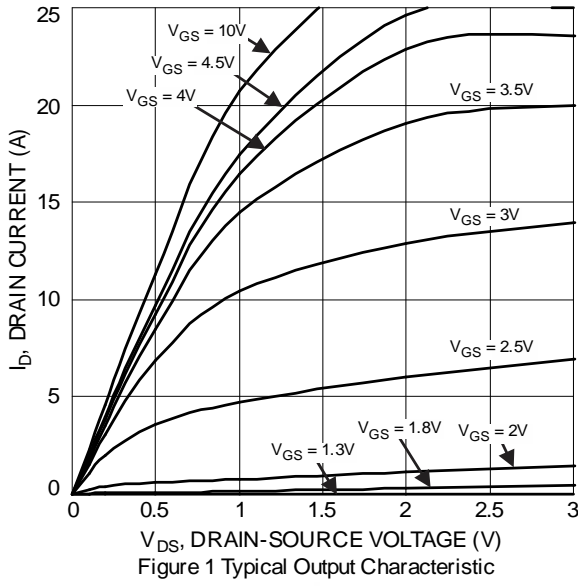
**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Total Power Dissipation (Note 5)			P <sub>D</sub>	0.49	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State		R <sub>θJA</sub>	254	°C/W
Total Power Dissipation (Note 6)			P <sub>D</sub>	0.65	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State		R <sub>θJA</sub>	191	°C/W
Operating and Storage Temperature Range			T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
Zero Gate Voltage Drain Current @T <sub>C</sub> = +25°C	I <sub>DSS</sub>	—	—	1.0	μA	V <sub>DS</sub> = 24V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	0.5	—	1.8	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	41	60	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 3.1A
		—	48	100		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 2A
		—	56	200		V <sub>GS</sub> = 3.3V, I <sub>D</sub> = 1.5A
Diode Forward Voltage	V <sub>SD</sub>	—	0.7	1	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 1A
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	C <sub>iss</sub>	—	278	—	pF	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V, f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	44	—	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	29	—	pF	
Gate Resistance	R <sub>g</sub>	—	4.2	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge	Q <sub>g</sub>	—	3.5	—	nC	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 3A
Gate-Source Charge	Q <sub>gs</sub>	—	0.1	—	nC	
Gate-Drain Charge	Q <sub>gd</sub>	—	1.3	—	nC	
Turn-On Delay Time	t <sub>D(ON)</sub>	—	5.7	—	ns	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 15V, R <sub>G</sub> = 3Ω, R <sub>L</sub> = 1.7Ω
Turn-On Rise Time	t <sub>R</sub>	—	97	—	ns	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	12.6	—	ns	
Turn-Off Fall Time	t <sub>F</sub>	—	51	—	ns	

- Notes:
- Device mounted on FR-4 substrate PC board, with minimum recommended pad layout.
  - Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to product testing.



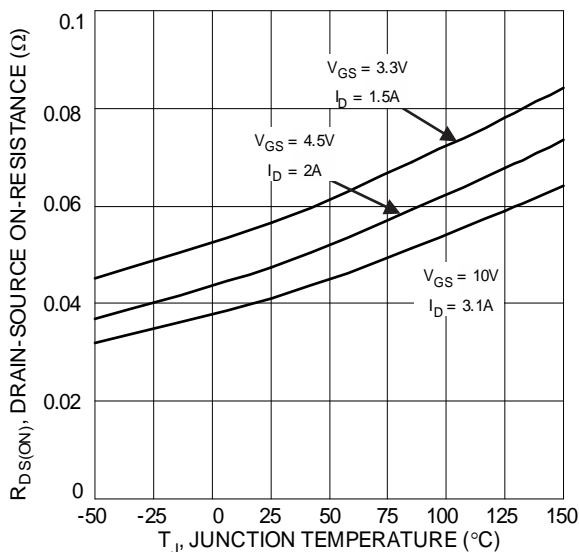


Figure 7 On-Resistance Variation with Temperature

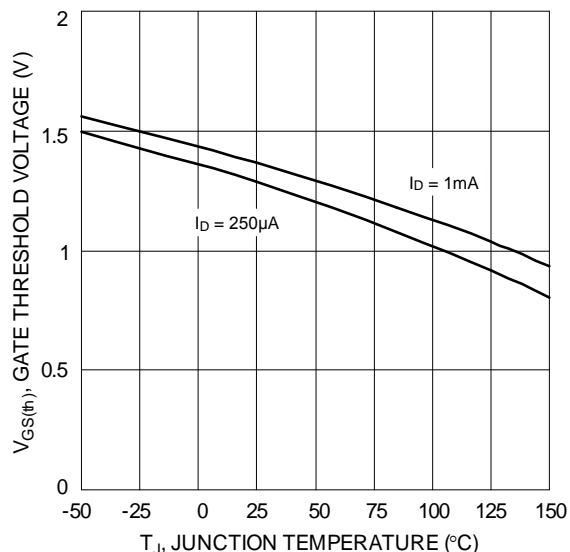


Figure 8 Gate Threshold Variation vs. Junction Temperature

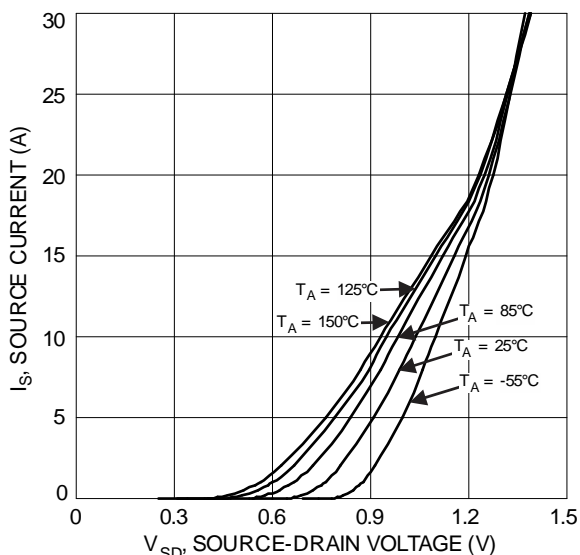


Figure 9 Diode Forward Voltage vs. Current

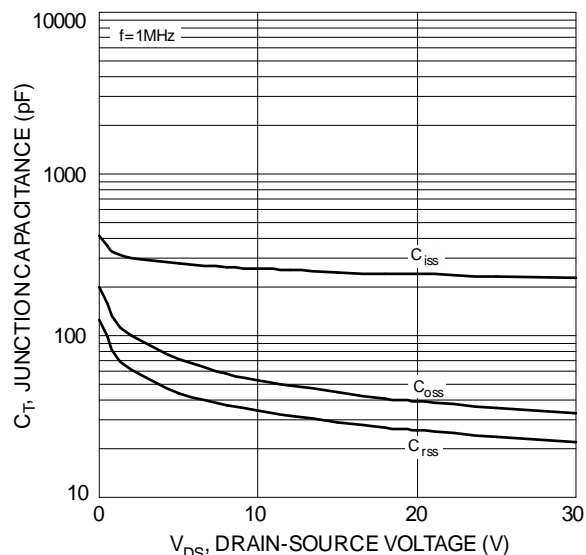


Figure 10 Typical Junction Capacitance

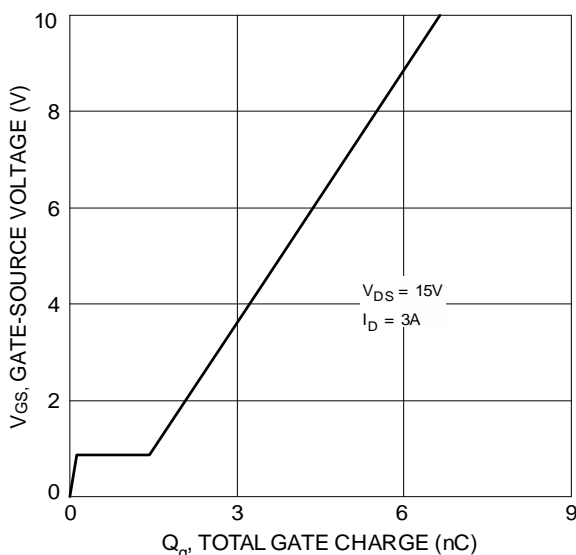


Figure 11 Gate Charge

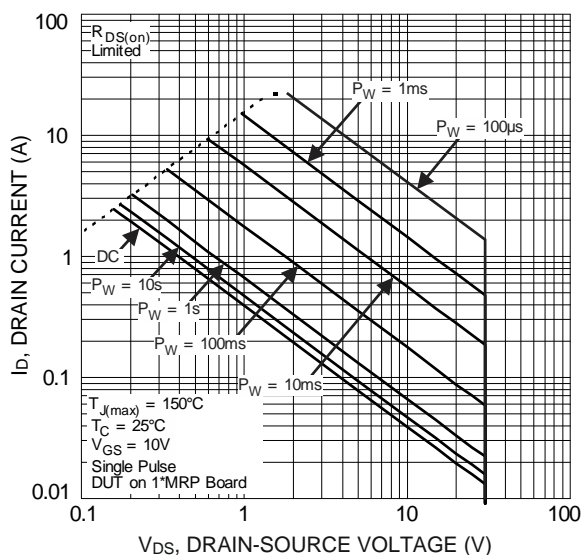


Figure 12 SOA, Safe Operation Area

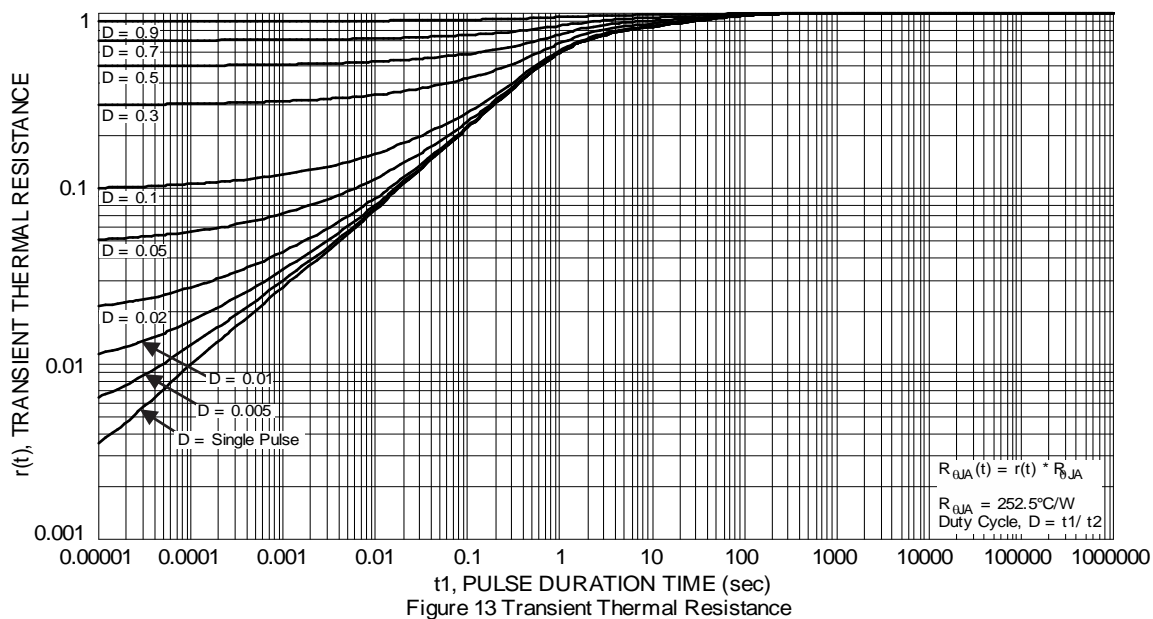
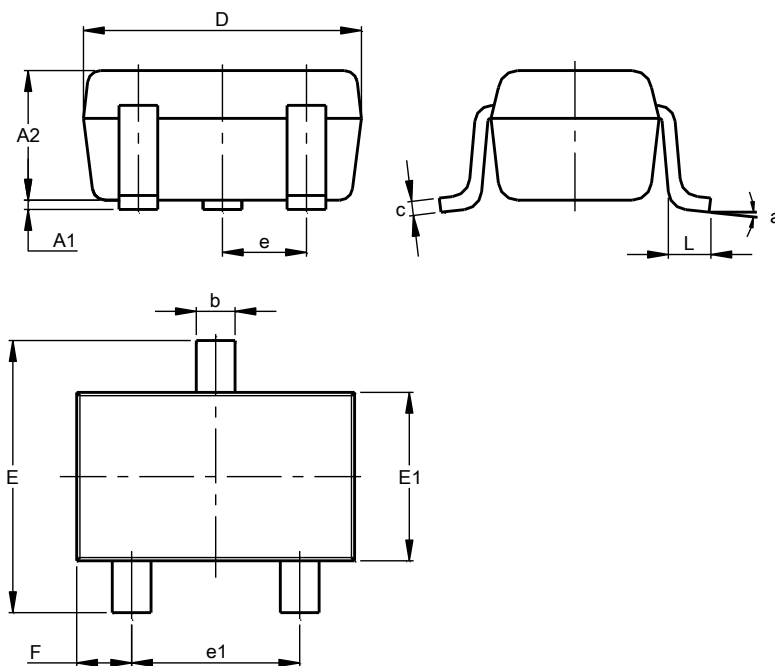


Figure 13 Transient Thermal Resistance

## Package Outline Dimensions

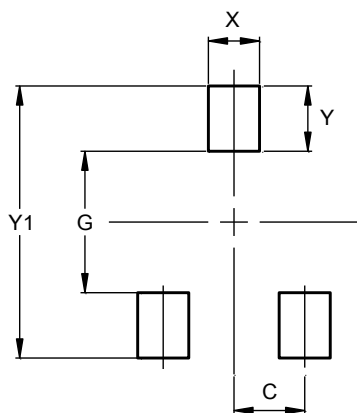
SOT323



SOT323			
Dim	Min	Max	Typ
A1	0.00	0.10	0.05
A2	0.90	1.00	0.95
b	0.25	0.40	0.30
c	0.10	0.18	0.11
D	1.80	2.20	2.15
E	2.00	2.20	2.10
E1	1.15	1.35	1.30
e	0.650 BSC		
e1	1.20	1.40	1.30
F	0.375	0.475	0.425
L	0.25	0.40	0.30
a	0°	8°	--
All Dimensions in mm			

## Suggested Pad Layout

SOT323



Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.470
Y	0.600
Y1	2.500